

Field Effect Transistor

Industrial Applications Unit in mm

Silicon N Channel MOS Type (t-MOS III.5)

High Speed, High Current DC-DC Converter,

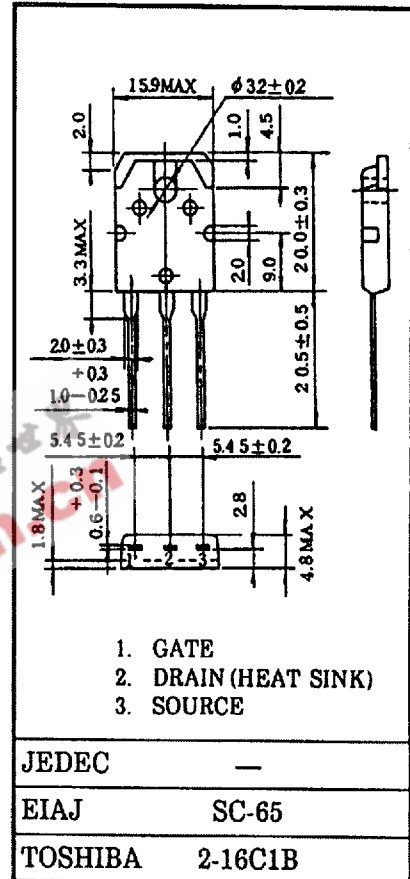
Relay Drive and Motor Drive Applications

Features

- Low Drain-Source ON Resistance
 - $R_{DS(ON)} = 0.38\Omega$ (Typ.)
- High Forward Transfer Admittance
 - $|Y_{fs}| = 7.0S$ (Typ.)
- Low Leakage Current
 - $I_{DSS} = 300\mu A$ (Max.) @ $V_{DS} = 500V$
- Enhancement-Mode
 - $V_{th} = 2.0 \sim 4.0V$ @ $V_{DS} = 10V, I_D = 1mA$

Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	500	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	500	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	15	A
	Pulse	I_{DP}	60
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	150	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$



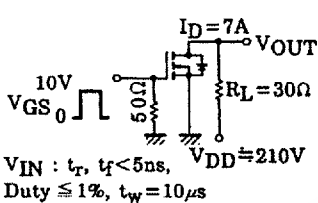
Weight : 4.6g

Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

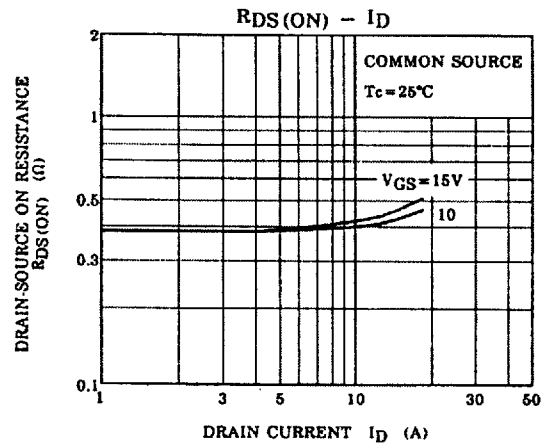
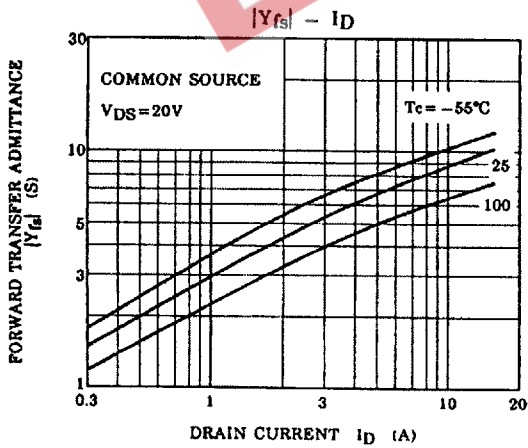
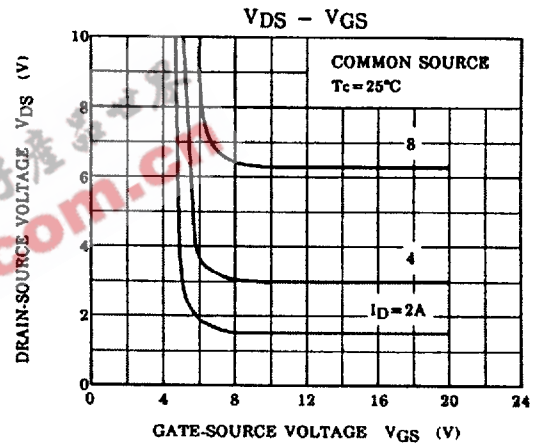
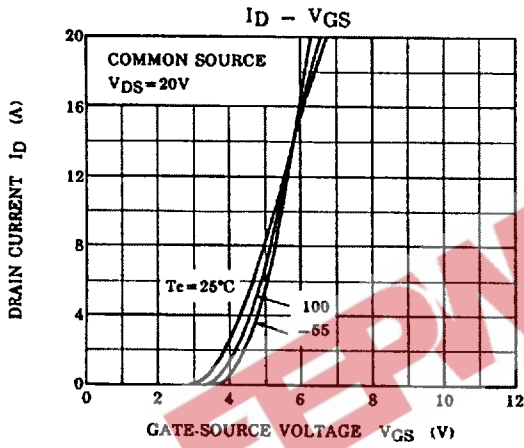
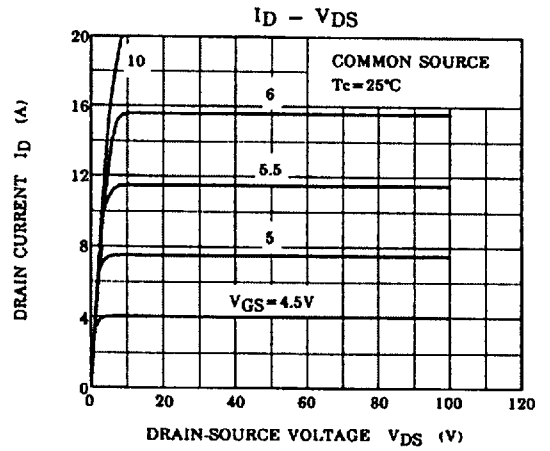
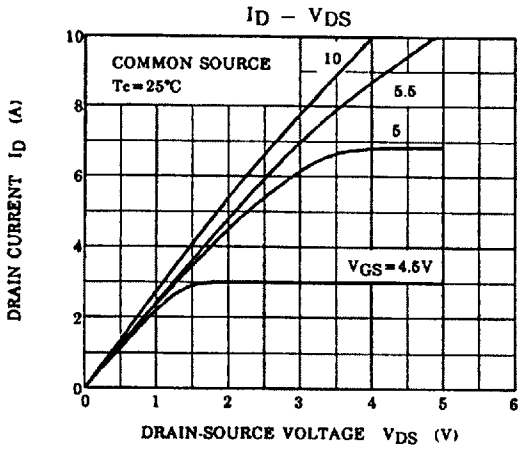
This transistor is an electrostatic sensitive device. Please handle with care.

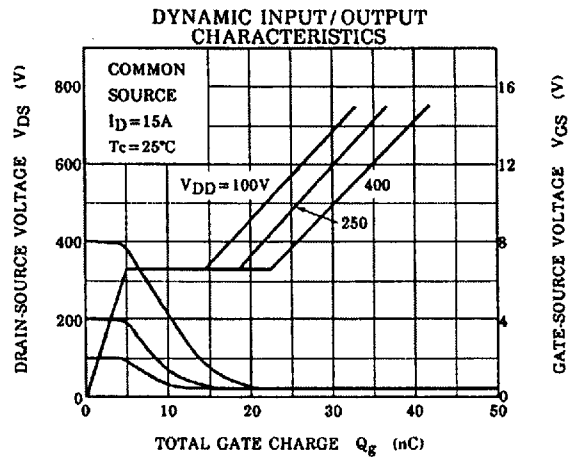
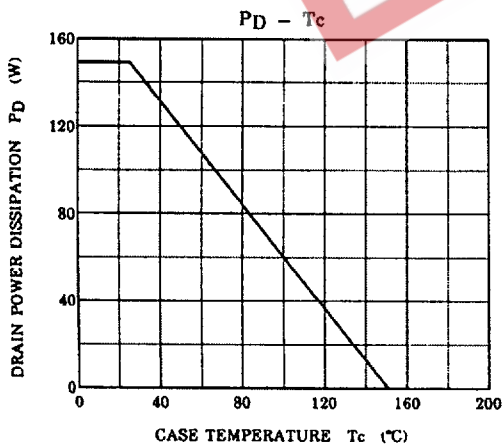
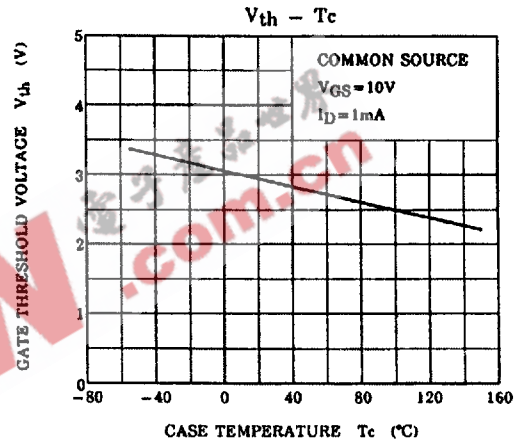
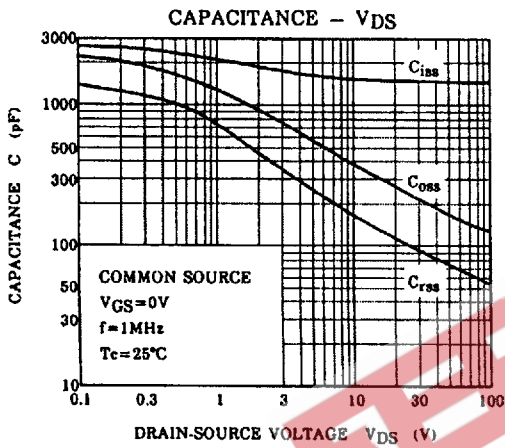
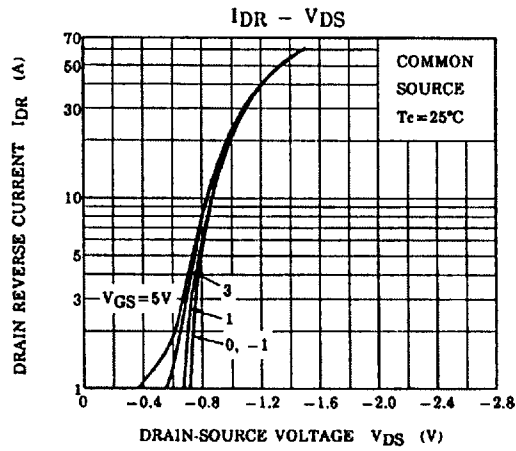
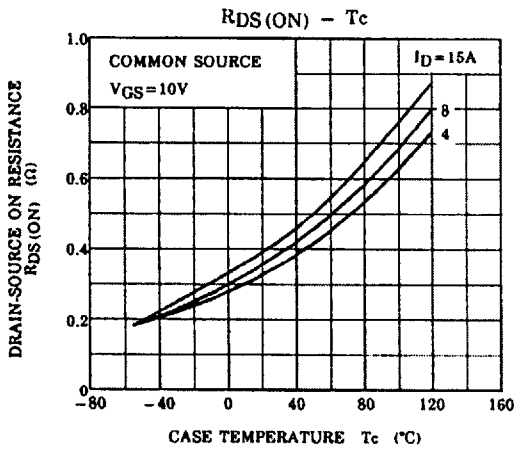
Electrical Characteristics (Ta = 25°C)

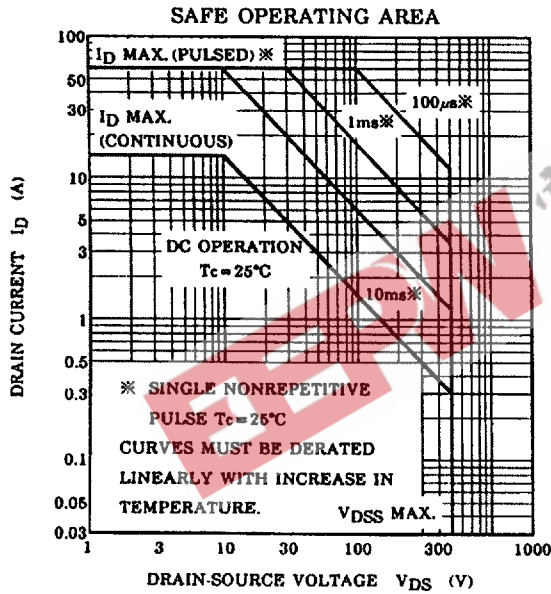
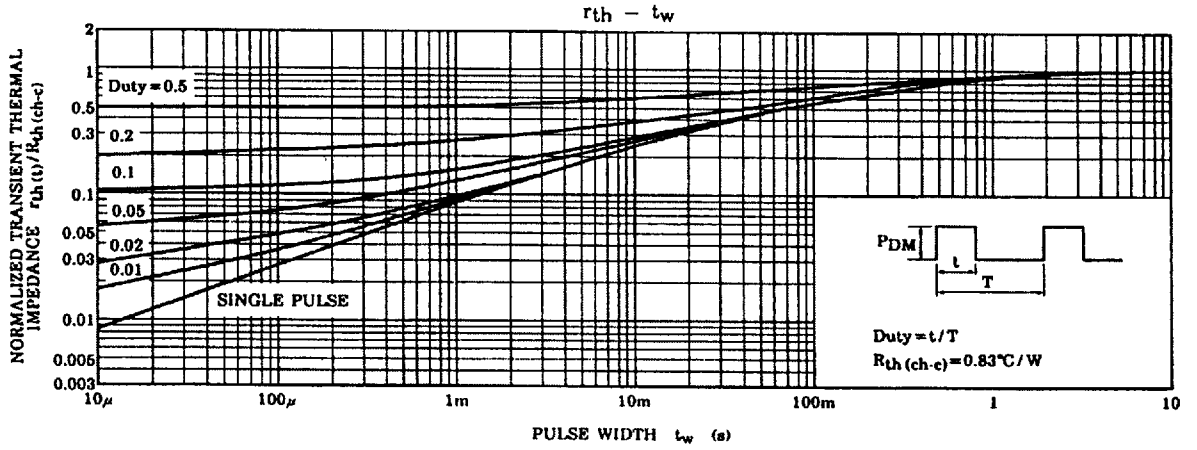
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0V$	-	-	± 100	nA	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 500V, V_{GS} = 0V$	-	-	300	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	500	-	-	V	
Gate Threshold Voltage	V_{th}	$V_{DS} = 10V, I_D = 1mA$	2.0	-	4.0	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D = 7A, V_{GS} = 10V$	-	0.38	0.45	Ω	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 7A$	6.0	7.0	-	S	
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1MHz$	-	1480	2300	pF	
Reverse Transfer Capacitance	C_{rss}		-	240	300		
Output Capacitance	C_{oss}		-	400	550		
Switching Time	Rise Time	t_r	-	90	180	ns	
	Turn-on Time	t_{on}	-	120	240		
	Fall Time	t_f	-	110	220		
	Turn-off Time	t_{off}	-	250	500		
							
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} = 400V, V_{GS} = 10V,$ $I_D = 15A$	-	60	75	nC	
Gate-Source Charge	Q_{gs}		-	25	-		
Gate-Drain ("Miller") Charge	Q_{gd}		-	35	-		

Source-Drain Diode Ratings and Characteristics (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	-	-	-	15	A
Pulse Drain Reverse Current	I_{DRP}	-	-	-	60	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 15A, V_{GS} = 0V$	-	-	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 15A, V_{GS} = 0V$ $di_{DR}/dt = 100A/\mu s$	-	750	-	ns
Reverse Recovered Charge	Q_{rr}		-	5.6	-	μC







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